



STP25NM50N - STF25NM50N STB25NM50N/-1 - STW25NM50N

N-CHANNEL 500V 0.11 Ω - 22 A TO-220/FP/D²/I²PAK/TO-247
SECOND GENERATION MDmesh™ MOSFET

Table 1: General Features

TYPE	V _{DSS} (@T _J MAX)	I _D	R _{DS(on)}
STB25NM50N-1	550V	22 A	0.140 Ω
STF25NM50N	550V	22 A(*)	0.140 Ω
STP25NM50N	550V	22 A	0.140 Ω
STW25NM50N	550V	22 A	0.140 Ω
STB25NM50N	550V	22 A	0.140 Ω

- HIGH dv/dt AND AVALANCHE CAPABILITIES
- 100% AVALANCHE TESTED
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE

DESCRIPTION

The **STx25NM50N** is realized with the second generation of MDmesh Technology. This revolutionary MOSFET associates a new vertical structure to the Company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters

APPLICATIONS

The MDmesh™ II family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.

Figure 1: Package

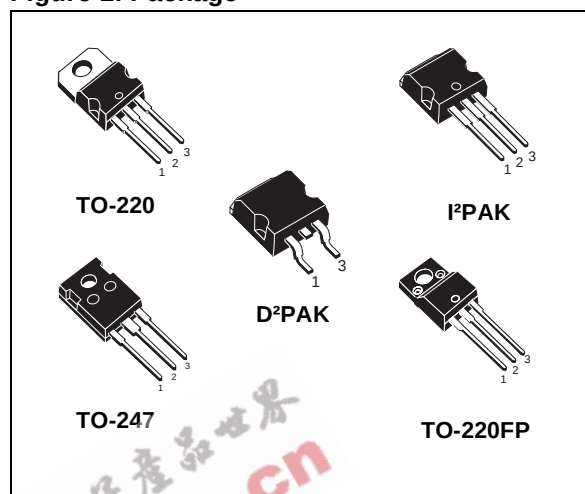


Figure 2: Internal Schematic Diagram

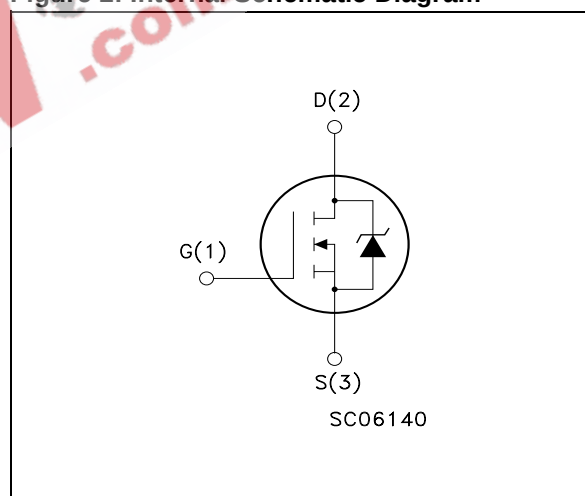


Table 2: Order Codes

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP25NM50N	P25NM50N	TO-220	TUBE
STF25NM50N	F25NM50N	TO-220FP	TUBE
STB25NM50N-1	B25NM50N	I²PAK	TUBE
STW25NM50N	W25NM50N	TO-247	TUBE
STB25NM50N	B25NM50N	D²PAK	TAPE & REEL

Table 3: Absolute Maximum ratings

Symbol	Parameter	Value		Unit
		TO-220/D ² PAK/I ² PAK/ TO-247	TO-220FP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	500		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	500		V
V _{GS}	Gate- source Voltage	±25		V
I _D	Drain Current (continuous) at T _C = 25°C	22	22(*)	A
I _D	Drain Current (continuous) at T _C = 100°C	14	14 (*)	A
I _{DM} (●)	Drain Current (pulsed)	88	88 (*)	A
P _{TOT}	Total Dissipation at T _C = 25°C	160	40	W
	Derating Factor	1.28	0.32	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	15		V/ns
T _{stg}	Storage Temperature	-55 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 22 A, di/dt ≤ 400 A/μs, V_{DD} = 80% V_{(BR)DSS}.

(*) Limited only by maximum temperature allowed

Table 4: Thermal Data

		TO-220/D ² PAK/I ² PAK/ TO-247	TO-220FP	
R _{thj-case}	Thermal Resistance Junction-case Max	0.78	3.1	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5		°C/W
T _l	Maximum Lead Temperature For Soldering Purpose	300		°C

Table 5: Avalanche Characteristics

Symbol	Parameter	Max Value	Unit
I _{AS}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	10	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AS} , V _{DD} = 50 V)	350	mJ

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^{\circ}\text{C}$ UNLESS OTHERWISE SPECIFIED)**Table 6: On/Off**

Symbol	Parameter	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 1\text{mA}$, $V_{GS} = 0$	500			V
$dv/dt(2)$	Drain Source Voltage Slope	$V_{DD} = 400\text{V}$, $I_D = 25\text{A}$, $V_{GS} = 10\text{V}$	44			V/ns
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$, $T_C = 125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 11\text{A}$		0.110	0.140	Ω

(2) Characteristic value at turn off on inductive load

Table 7: Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (1)$	Forward Transconductance	$V_{DS} = 15\text{V}$, $I_D = 11\text{A}$		19		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{V}$, $f = 1\text{MHz}$, $V_{GS} = 0$		2565 511 77		pF pF pF
$C_{oss\text{ eq.}} (*)$	Equivalent Output Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V to } 400\text{V}$		315		pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on Delay Time Rise Time Off-voltage Rise Time Fall Time	$V_{DD} = 250\text{V}$, $I_D = 11\text{A}$ $R_G = 4.7\Omega$, $V_{GS} = 10\text{V}$ (see Figure 19)		23 23 75 22		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 400\text{V}$, $I_D = 22\text{A}$, $V_{GS} = 10\text{V}$, (see Figure 23)		84 11 35		nC nC nC
R_g	Gate Input Resistance	$f = 1\text{MHz}$ Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.6		Ω

Table 8: Source Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				22 88	A A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 22\text{A}$, $V_{GS} = 0$			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 22\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$ $V_{DD} = 100\text{V}$, $T_J = 25^{\circ}\text{C}$ (see Figure 21)		460 6.9 30		ns μC A
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 22\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$ $V_{DD} = 100\text{V}$, $T_J = 150^{\circ}\text{C}$ (see Figure 21)		532 8.25 31		ns μC A

(1) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.(*) $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DS}

Figure 3: Safe Operating Area For TO-220/
I²PAK/D²PAK

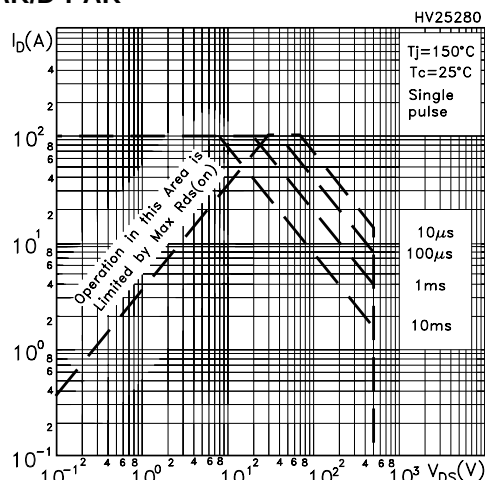


Figure 4: Safe Operating Area For TO-220FP

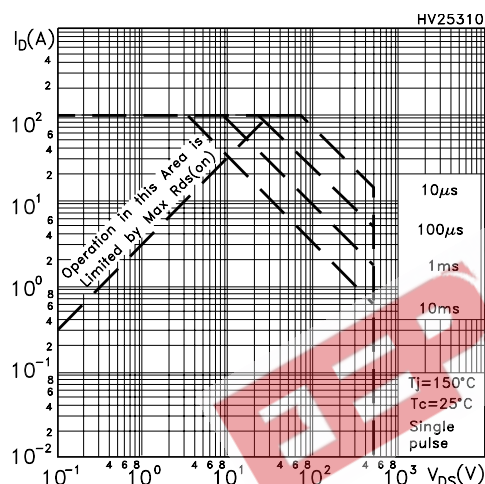


Figure 5: Safe Operating Area For TO-247

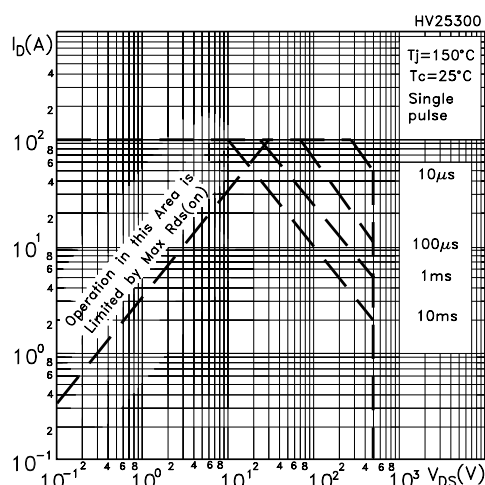


Figure 6: Thermal Impedance TO-220/I²PAK/
D²PAK

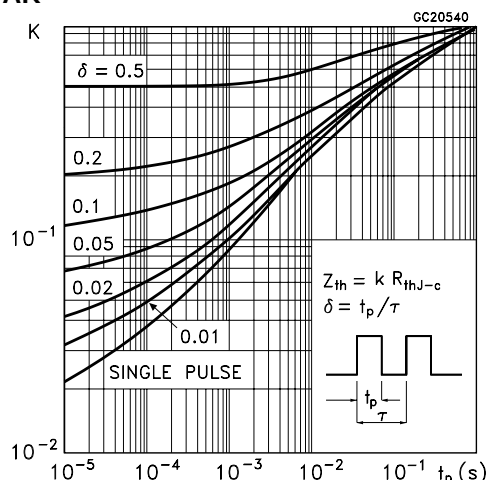


Figure 7: Thermal Impedance For TO-220FP

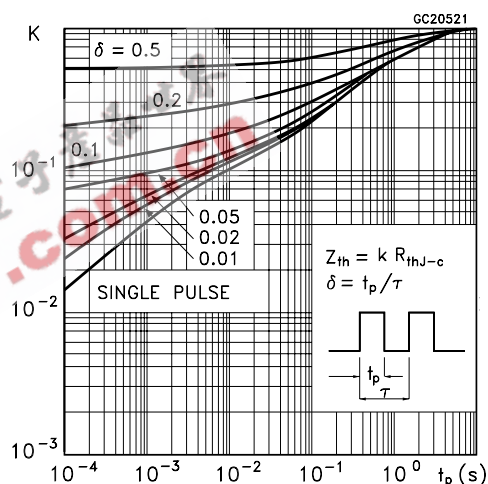


Figure 8: Thermal Impedance For TO-247

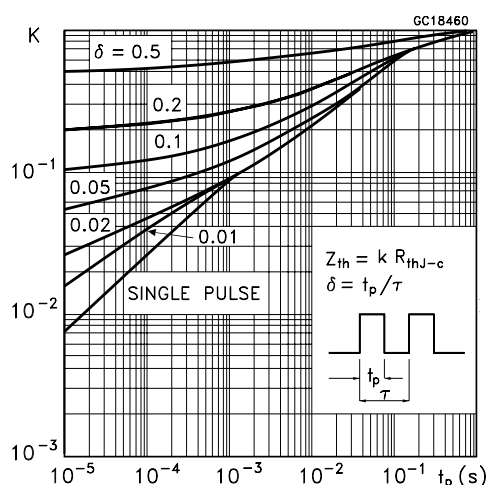


Figure 9: Output Characteristics

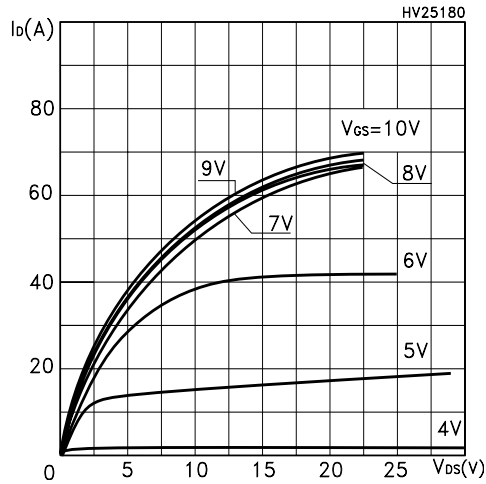


Figure 10: Transconductance

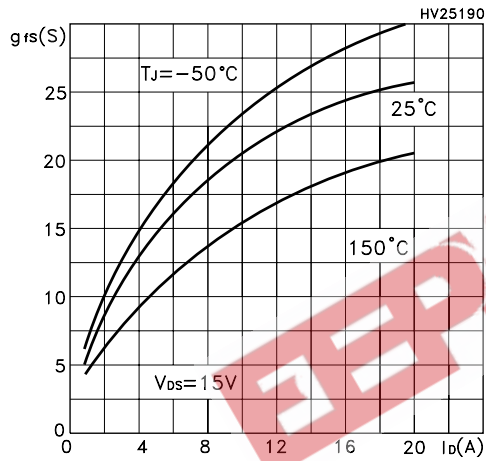


Figure 11: Gate Charge vs Gate-source Voltage

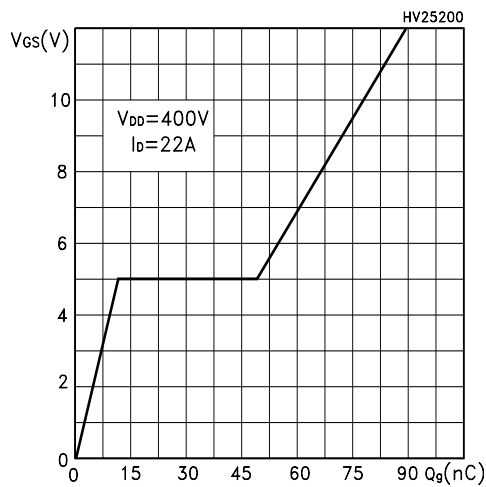


Figure 12: Transfer Characteristics

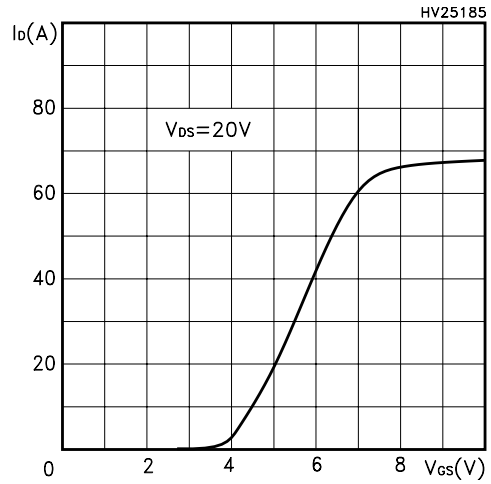


Figure 13: Static Drain-Source On Resistance

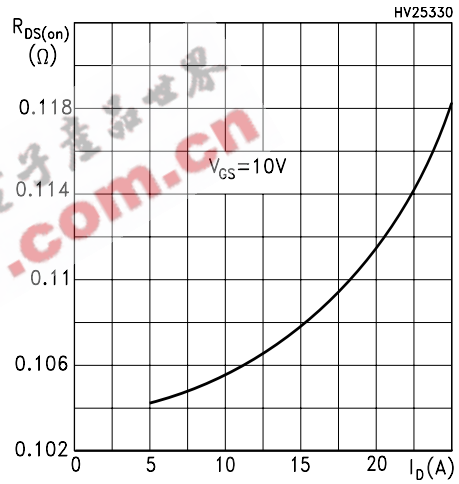


Figure 14: Capacitance Variations

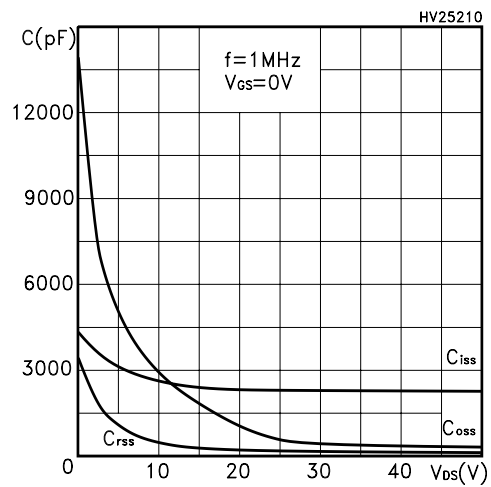


Figure 15: Normalized Gate Threshold Voltage vs Temperature

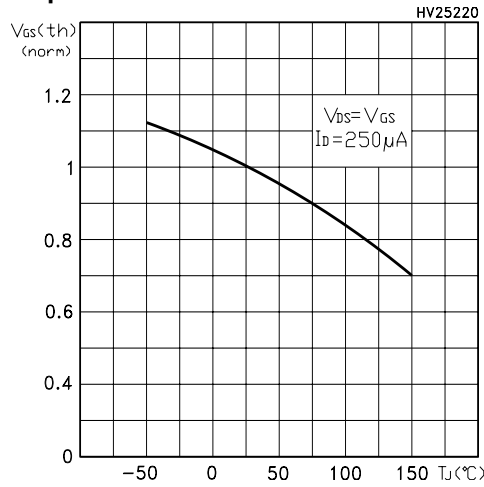


Figure 17: Normalized On Resistance vs Temperature

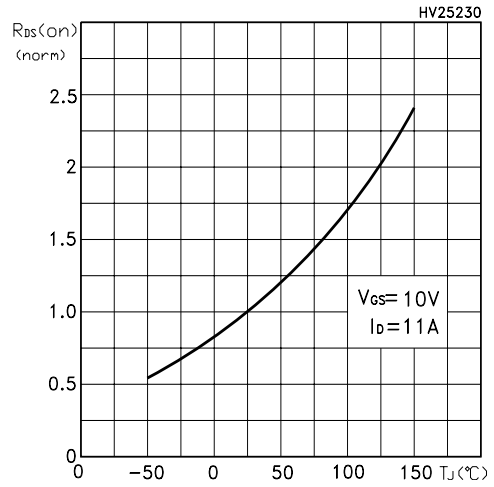


Figure 16: Source-Drain Forward Characteristics

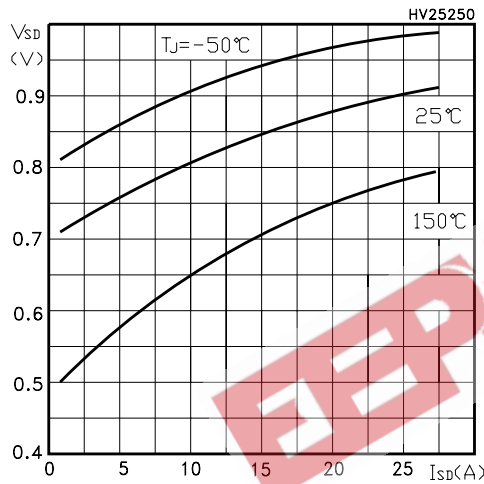


Figure 18: Normalized BV_{DSS} vs Temperature

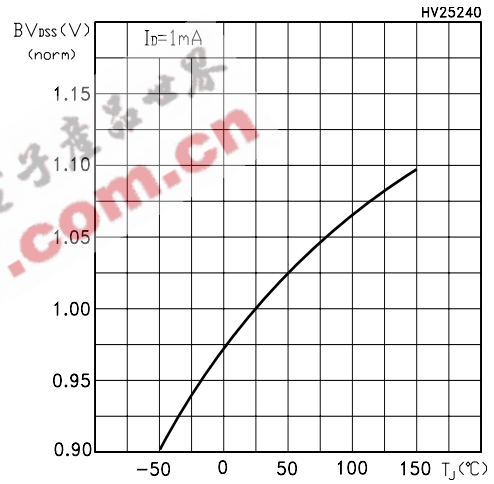


Figure 19: Unclamped Inductive Load Test Circuit

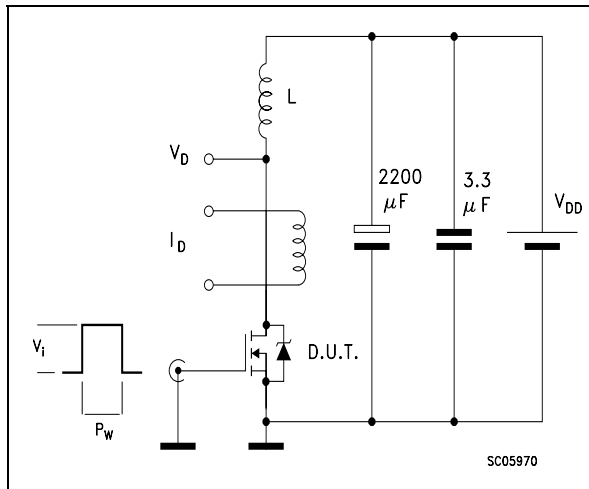


Figure 20: Switching Times Test Circuit For Resistive Load

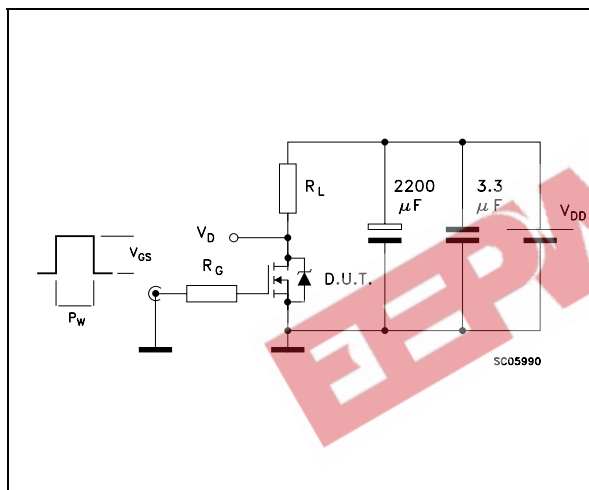


Figure 21: Test Circuit For Inductive Load Switching and Diode Recovery Times

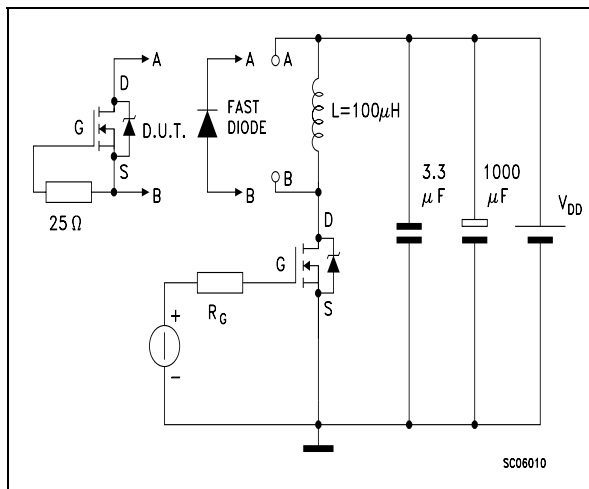


Figure 22: Unclamped Inductive Wafeform

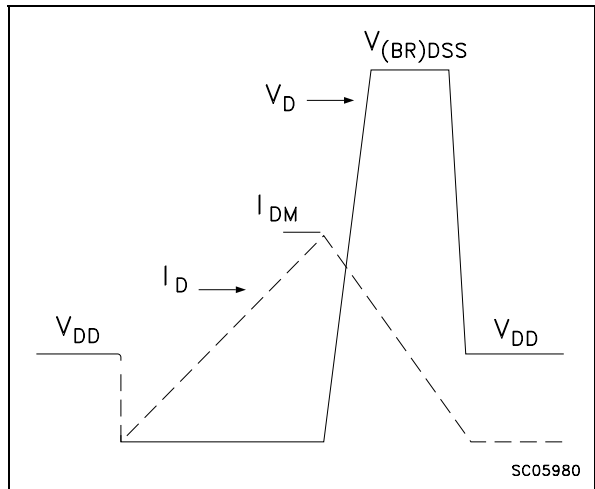
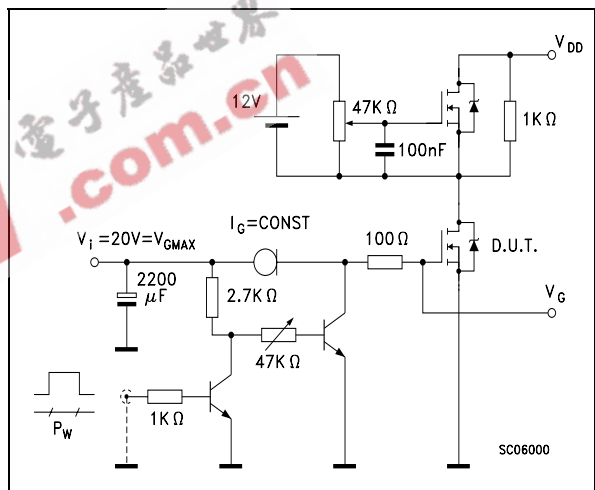


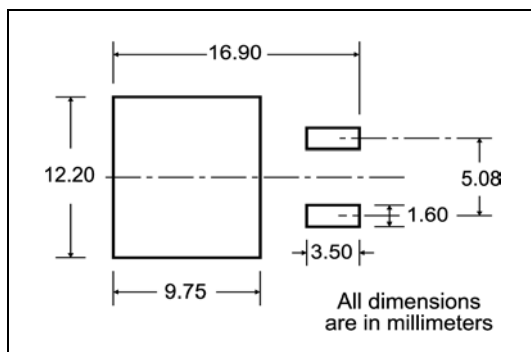
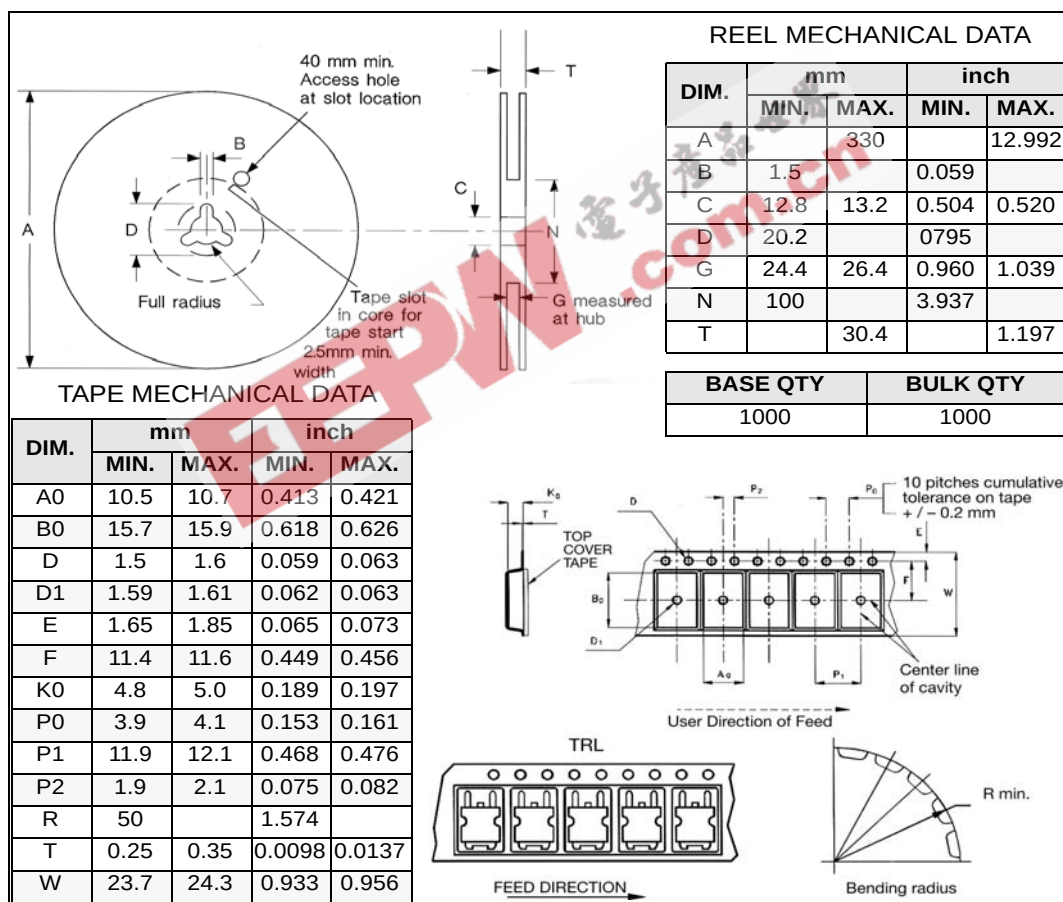
Figure 23: Gate Charge Test Circuit



STP25NM50N - STF25NM50N - STB25NM50N/-1 - STW25NM50N

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

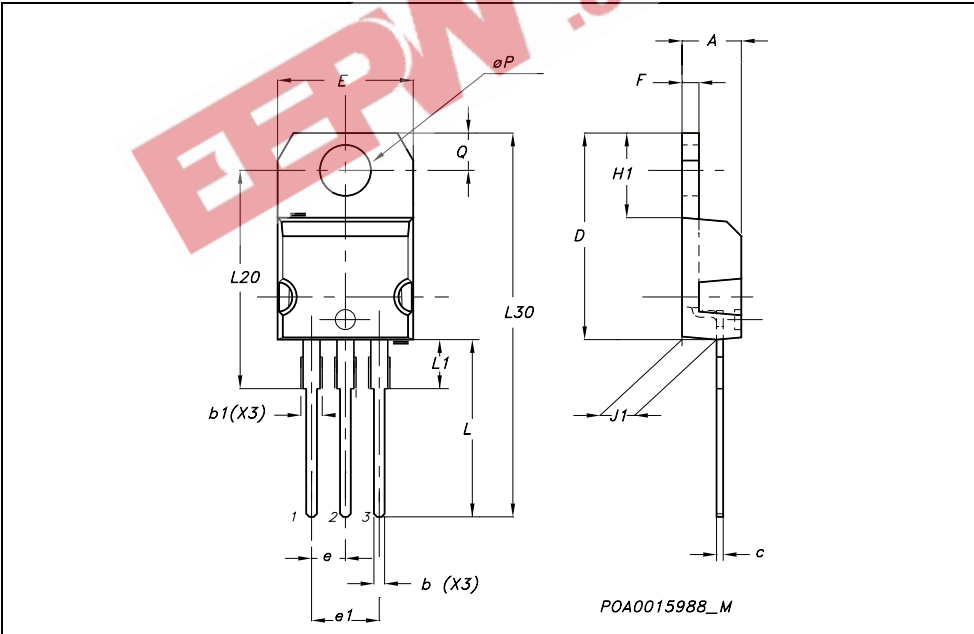
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D²PAK FOOTPRINT**TAPE AND REEL SHIPMENT**

* on sales type

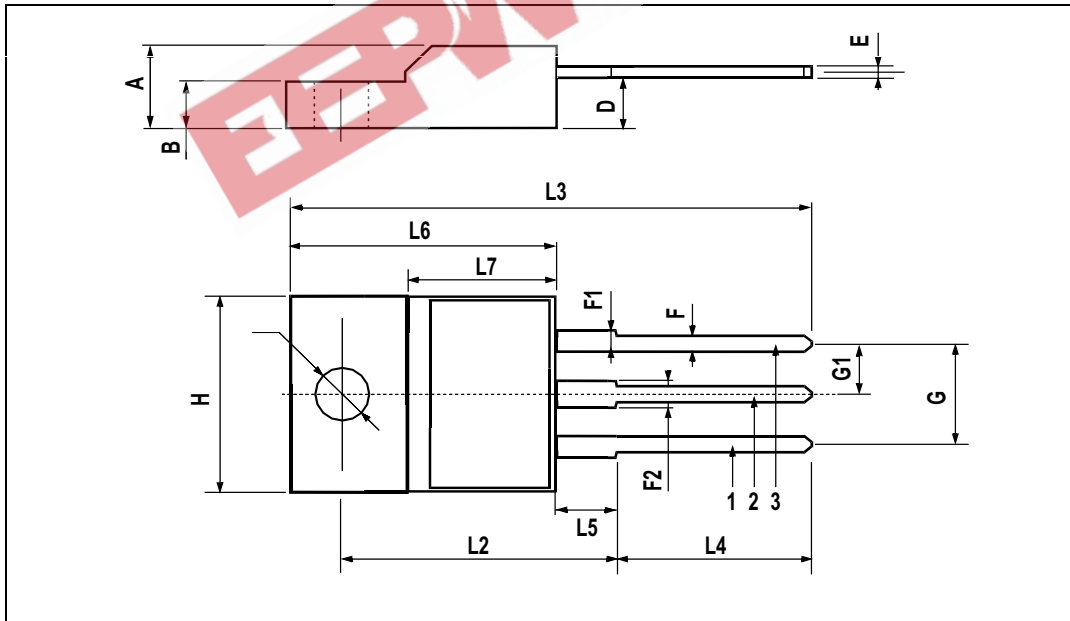
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



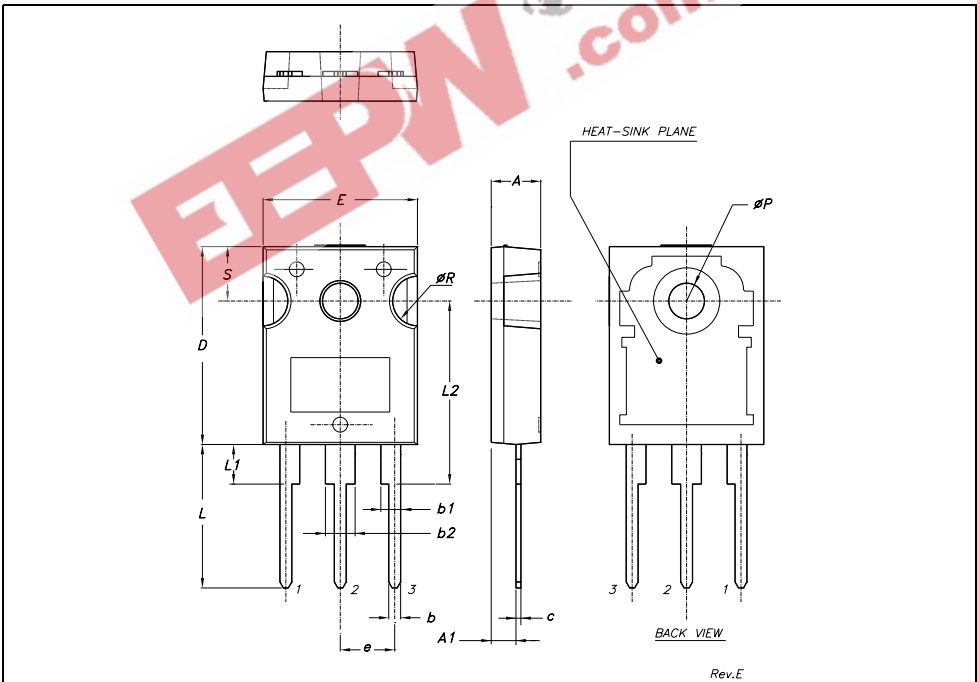
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



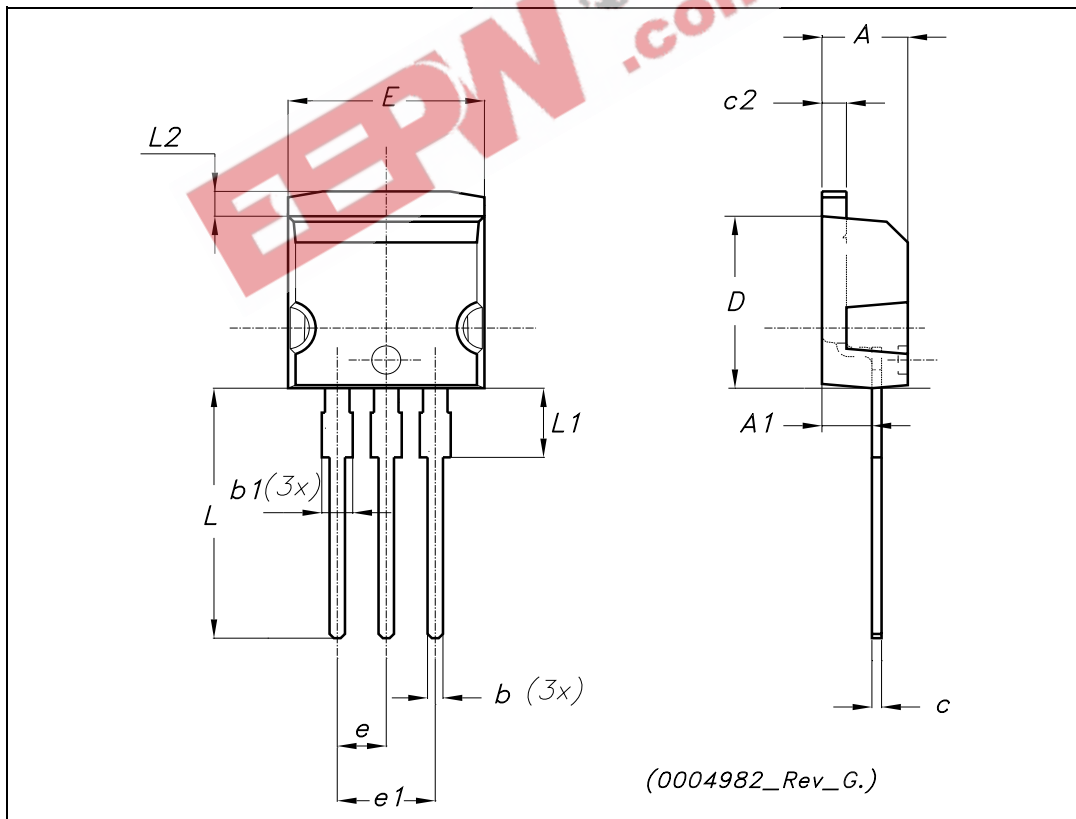
TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			

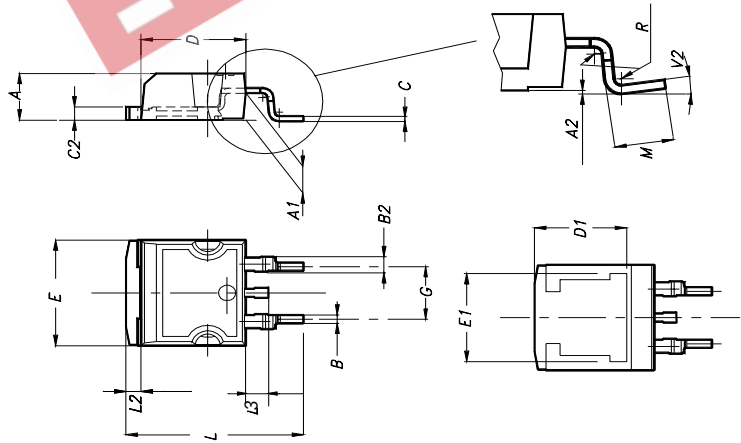


Table 9: Revision History

Date	Revision	Description of Changes
30-Nov-2004	1	First Release.
08-Mar-2005	2	Inserted Curves
22-Mar-2005	3	Modified title
13-Apr-2005	4	Modified some values
28-Apr-2005	5	Modified some values in Table 8
16-May-2005	6	Modified values in tab7
17-Jun-2005	7	Inserted new row in table 6
07-Sep-2005	8	Inserted ecopack indication
05-Oct-2005	9	Modified curves 9-12

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